# 500 mA, 40 V Schottky **Barrier Diode**

These Schottky barrier diodes are optimized for low forward voltage drop and low leakage current that offers the most optimal power dissipation in applications. They are housed in spacing saving micro-packaging ideal for space constraint applications.

### **Features**

- Low Forward Voltage Drop -530 mV (Typ.) @  $I_F = 500 \text{ mA}$
- Low Reverse Current 3.0  $\mu$ A (Typ.) @  $V_R = 40 \text{ V}$
- 500 mA of Continuous Forward Current
- ESD Rating: Human Body Model: Class 3B - Charged Device Model: Class IV
- High Switching Speed
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

# **Typical Applications**

- LCD and Keypad Backlighting
- Camera Photo Flash
- Buck and Boost dc-dc Converters
- Reverse Voltage and Current Protection
- Clamping & Protection

# **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	40	V
Forward Current (DC)	IF	500	mA
Forward Surge Current (60 Hz @ 1 cycle)	I <sub>FSM</sub>	3.0	А
Repetitive Peak Forward Current (Pulse Wave = 1 sec, Duty Cycle = 66%)	I <sub>FRM</sub>	1.5	А
ESD Rating: Human Body Model Charged Device Model	ESD	> 8 > 1	kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



# ON Semiconductor®

www.onsemi.com



DIAGRAM

**MARKING** 

**CASE 502** 

Μ

ΥK = Specific Device Code Date Code



### ORDERING INFORMATION

Device	Package	Shipping†
NSR05T40XV2T5G	SOD-523 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Thermal Resistance Junction–to–Ambient (Note 1) Total Power Dissipation @ T <sub>A</sub> = 25°C	R <sub>θJA</sub> P <sub>D</sub>			489 250	°C/W mW
Thermal Resistance Junction–to–Ambient (Note 2) Total Power Dissipation @ T <sub>A</sub> = 25°C				358 350	°C/W mW
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>		-55 to +150		°C

- 1. Mounted onto a 4 in square FR-4 board 50 mm sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.
- 2. Mounted onto a 4 in square FR-4 board 650 mm sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.

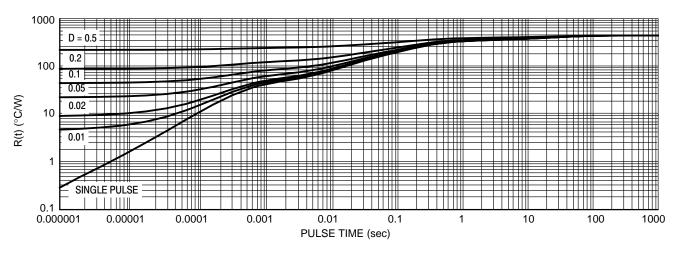


Figure 1. Thermal Response (Note 1)

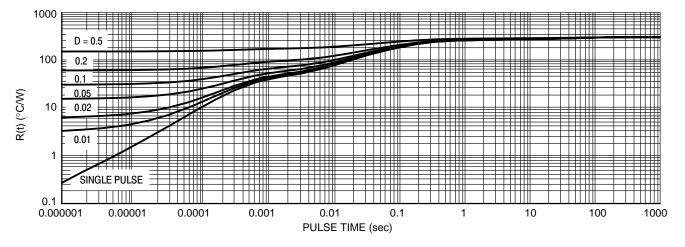
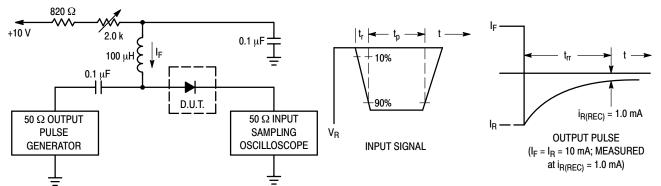


Figure 2. Thermal Response (Note 2)

# $\textbf{ELECTRICAL CHARACTERISTICS} \ (T_A = 25^{\circ}C \ unless \ otherwise \ noted)$

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Leakage (V <sub>R</sub> = 10 V) (V <sub>R</sub> = 40 V)	I <sub>R</sub>		0.5 3.0	5.0 55	μΑ
Forward Voltage (I <sub>F</sub> = 10 mA) (I <sub>F</sub> = 100 mA) (I <sub>F</sub> = 200 mA) (I <sub>F</sub> = 500 mA)	V <sub>F</sub>		360 420 450 530	400 465 525 640	mV
Total Capacitance (V <sub>R</sub> = 1.0 V, f = 1.0 MHz)	C <sub>T</sub>		70		pF
Reverse Recovery Time $(I_F = I_R = 10 \text{ mA}, I_{R(REC)} = 1.0 \text{ mA}, Figure 3)$	t <sub>rr</sub>		20		ns
Peak Forward Recovery Voltage (I <sub>F</sub> = 100 mA, t <sub>r</sub> = 20 ns, Figure 4)	V <sub>FRM</sub>		540		mV



Notes: 1. A 2.0  $k\Omega$  variable resistor adjusted for a Forward Current (IF) of 10 mA.

- 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10 mA.
- $3. t_n * t_m$

Figure 3. Recovery Time Equivalent Test Circuit

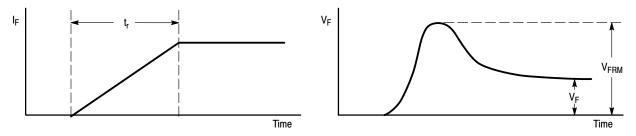


Figure 4. Peak Forward Recovery Voltage Definition

### **TYPICAL CHARACTERISTICS**

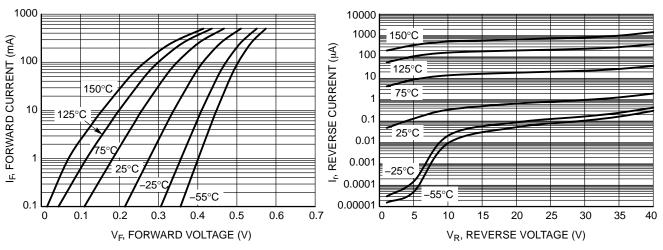


Figure 5. Forward Voltage

Figure 6. Leakage Current

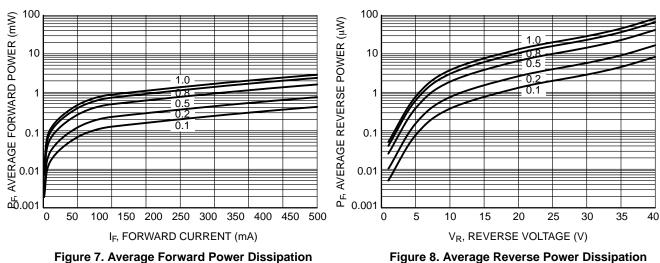


Figure 7. Average Forward Power Dissipation

C<sub>T</sub>, TOTAL CAPACITANCE (pF)

I<sub>FSM</sub>, FORWARD SURGE MAX CURRENT (A) Based on square wave currents T<sub>J</sub> = 25°C prior to surge 0.001 0.01 t<sub>P</sub>, PULSE ON TIME (ms)

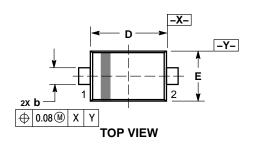
Figure 9. Total Capacitance

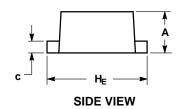
Figure 10. Forward Surge Current

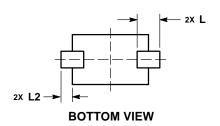
f = 1.0 MHz

### PACKAGE DIMENSIONS

SOD-523 **CASE 502** ISSUE E







#### NOTES:

- NOTES.

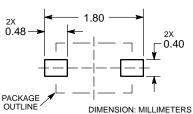
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PRO-
- TRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	NOM MA		
Α	0.50	0.60	0.70	
b	0.25	0.30	0.35	
С	0.07	0.14	0.20	
D	1.10	1.20	1.30	
E	0.70	0.80	0.90	
HE	1.50	1.60	1.70	
L	0.30 REF			
L2	0.15	0.20	0.25	

### RECOMMENDED **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and the unarregistered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

### **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada

Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center

Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative